

2SJ486

Silicon P Channel MOS FET

REJ03G0869-0300
(Previous: ADE-208-512A)
Rev.3.00
Sep 07, 2005

Description

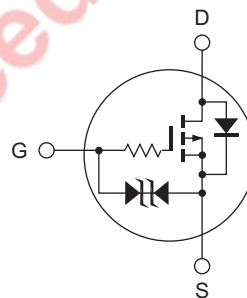
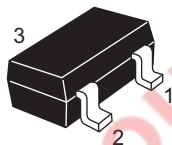
Low frequency power switching

Features

- Low on-resistance
 $R_{DS(on)} = 0.5 \Omega$ typ. (at $V_{GS} = -4 \text{ V}$, $I_D = -100 \text{ mA}$)
- 2.5 V gate drive devices.
- Small package (MPAK).

Outline

RENESAS Package code: PLSP0003ZB-A
(Package name: MPAK)



1. Source
2. Gate
3. Drain

Note: Marking is "ZU-".

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	-30	V
Gate to source voltage	V_{GSS}	± 10	V
Drain current	I_D	-0.3	A
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	-0.6	A
Channel dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. PW \leq 100 μ s, duty cycle \leq 10%

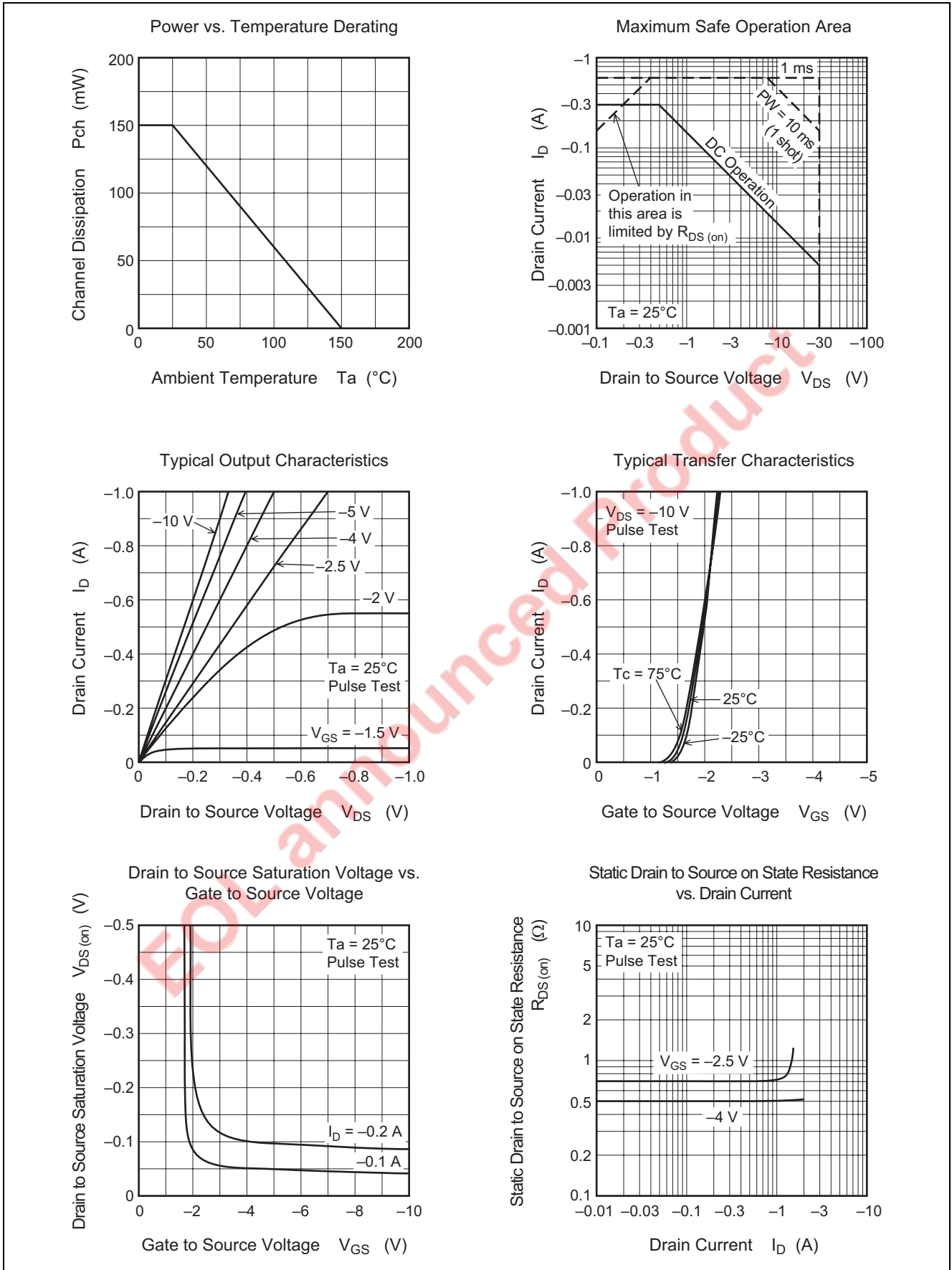
Electrical Characteristics

(Ta = 25°C)

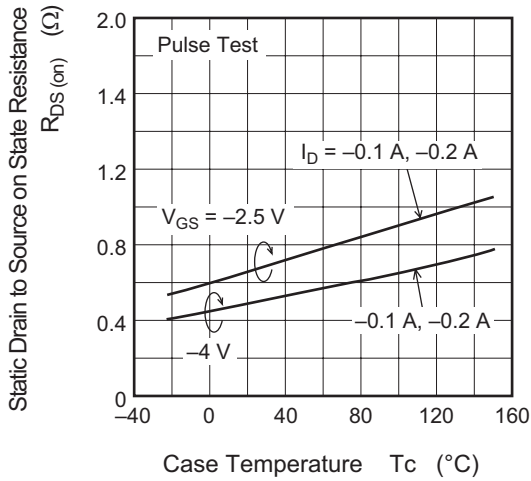
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10 \mu A, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 10	—	—	V	$I_G = \pm 100 \mu A, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-1.0	μA	$V_{DS} = -30 V, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 5.0	μA	$V_{GS} = \pm 6.5 V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.5	—	-1.5	V	$I_D = -10 \mu A, V_{DS} = -5 V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.5	0.65	Ω	$I_D = -100 mA, V_{GS} = -4 V$ ^{Note 2}
	$R_{DS(on)}$	—	0.7	1.2	Ω	$I_D = -100 mA, V_{GS} = -2.5 V$ ^{Note 2}
Forward transfer admittance	$ y_{fs} $	0.4	0.65	—	S	$I_D = -100 mA, V_{DS} = -10 V$ ^{Note 2}
Input capacitance	C_{iss}	—	45	—	pF	$V_{DS} = -10 V$
Output capacitance	C_{oss}	—	76	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	5.4	—	pF	$f = 1 MHz$
Turn-on delay time	$t_{d(on)}$	—	120	—	ns	$V_{GS} = -4 V$
Rise time	t_r	—	340	—	ns	$I_D = -150 mA$
Turn-off delay time	$t_{d(off)}$	—	850	—	ns	$R_L = 66.6 \Omega$
Fall time	t_f	—	550	—	ns	

Note: 2. Pulse test

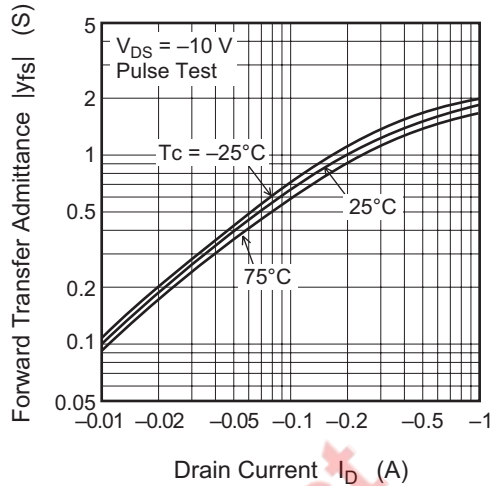
Main Characteristics



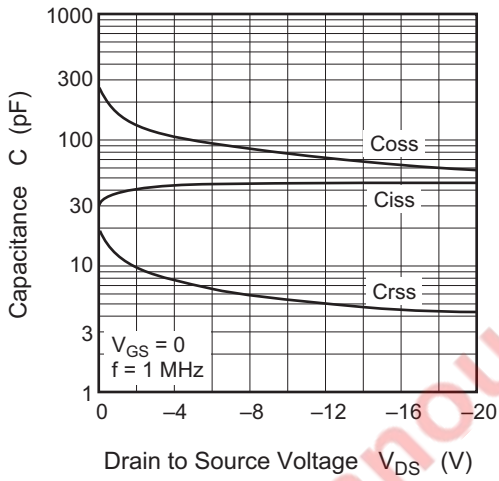
Static Drain to Source on State Resistance vs. Temperature



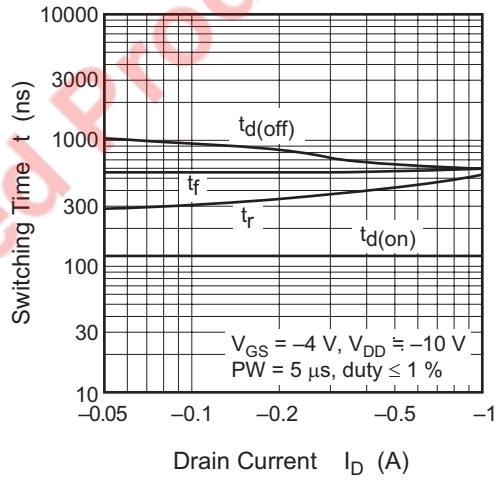
Forward Transfer Admittance vs. Drain Current



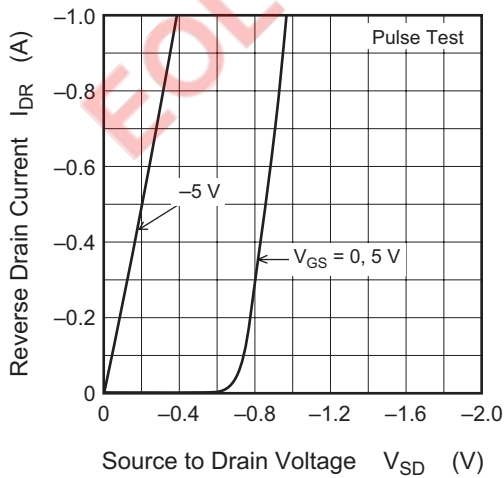
Typical Capacitance vs. Drain to Source Voltage

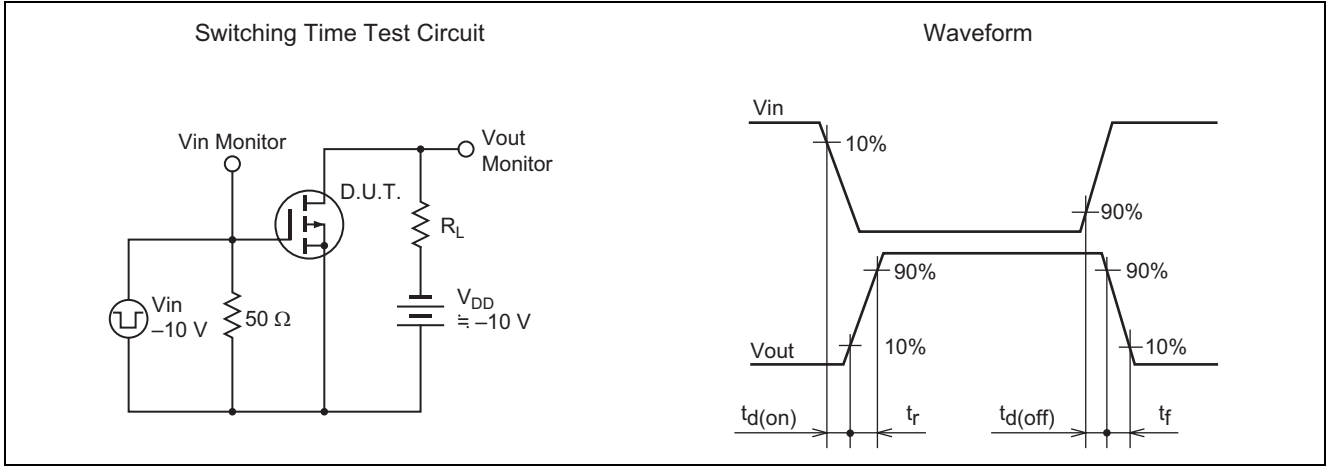


Switching Characteristics



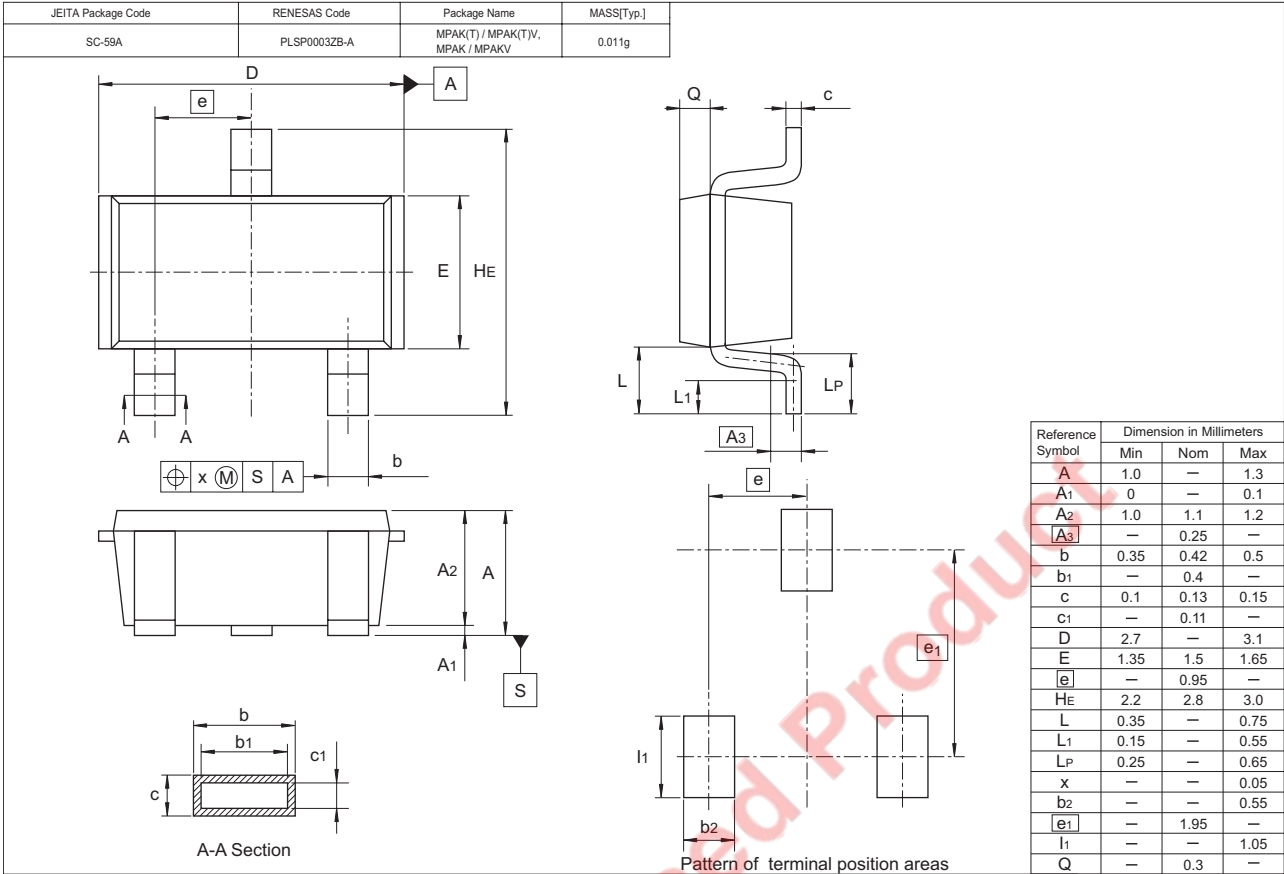
Reverse Drain Current vs. Source to Drain Voltage





EOL announced Product

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SJ486ZU-TL-E	3000 pcs	Taping
2SJ486ZU-TR-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510